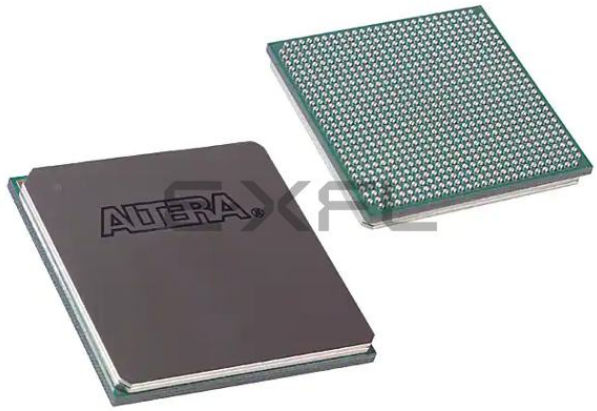

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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details	
Product Status	Obsolete
Number of LABs/CLBs	4125
Number of Logic Elements/Cells	41250
Total RAM Bits	3423744
Number of I/O	615
Number of Gates	-
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	780-BBGA, FCBGA
Supplier Device Package	780-FBGA (29x29)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep1s40f780c8n

1. Introduction

S51001-3.2

Introduction

The Stratix® family of FPGAs is based on a 1.5-V, 0.13-µm, all-layer copper SRAM process, with densities of up to 79,040 logic elements (LEs) and up to 7.5 Mbits of RAM. Stratix devices offer up to 22 digital signal processing (DSP) blocks with up to 176 (9-bit × 9-bit) embedded multipliers, optimized for DSP applications that enable efficient implementation of high-performance filters and multipliers. Stratix devices support various I/O standards and also offer a complete clock management solution with its hierarchical clock structure with up to 420-MHz performance and up to 12 phase-locked loops (PLLs).

The following shows the main sections in the Stratix Device Family Data Sheet:

Figure 2–17. M4K RAM Block Control Signals

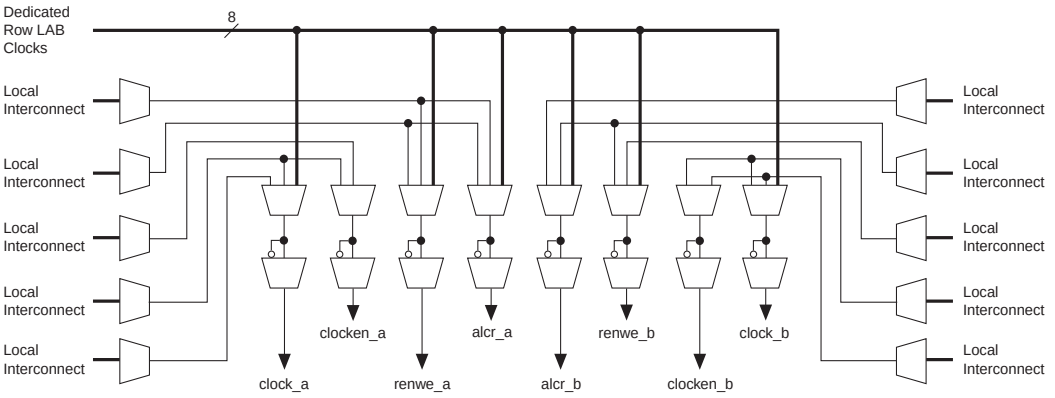


Figure 2–18. M4K RAM Block LAB Row Interface

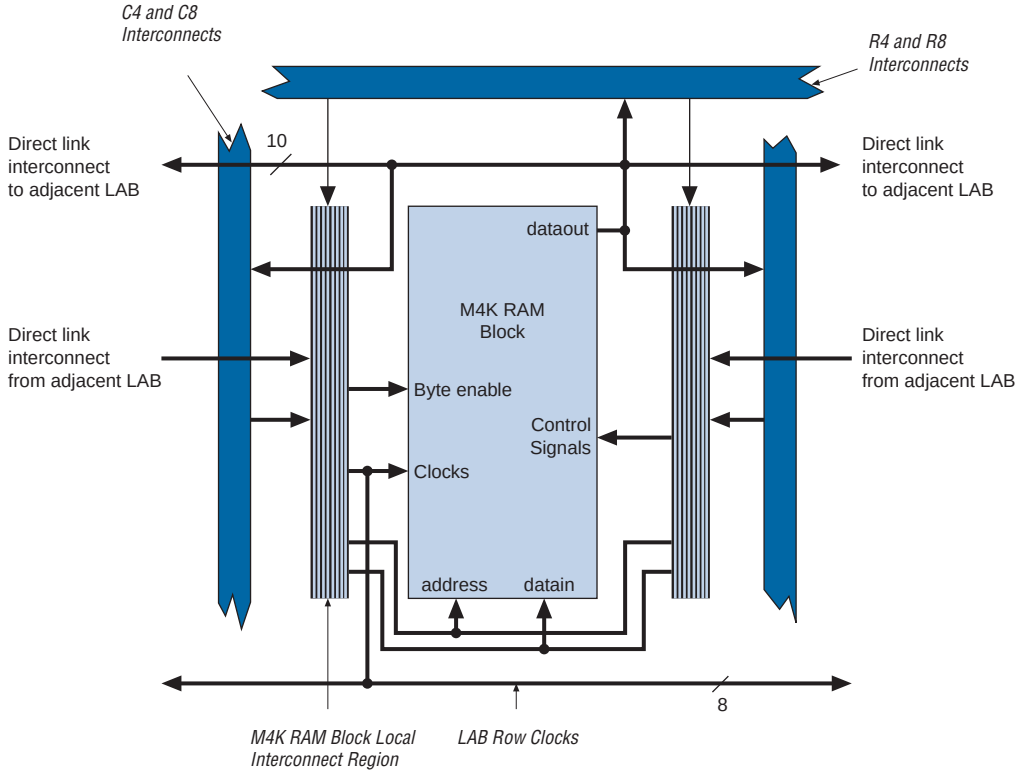
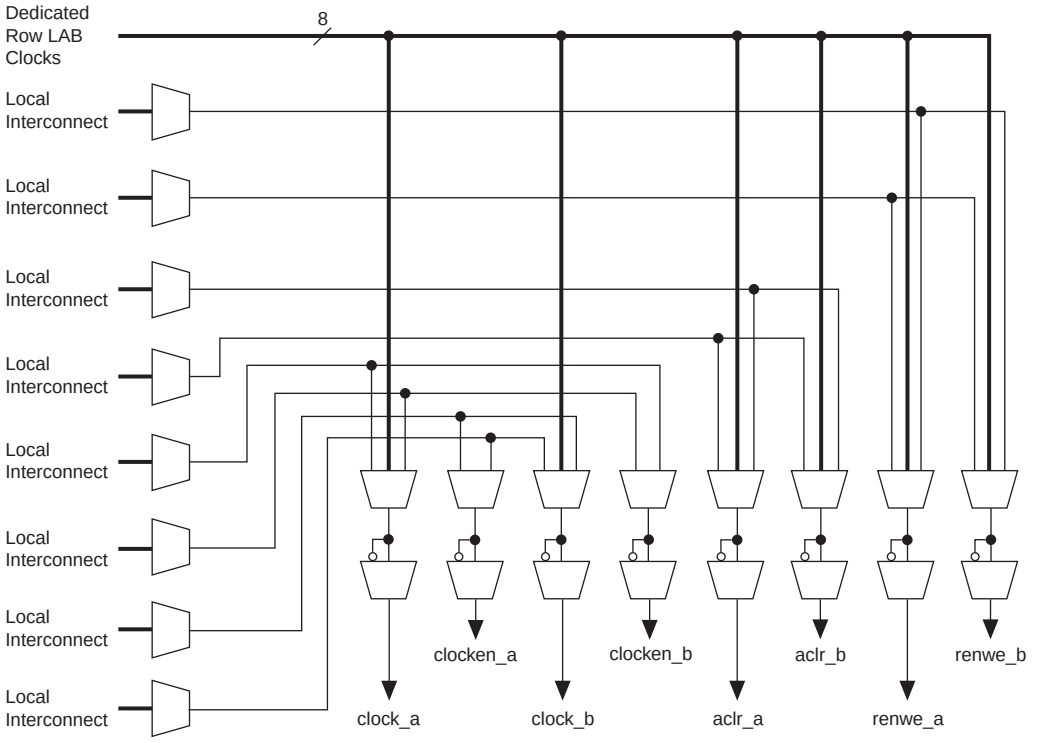
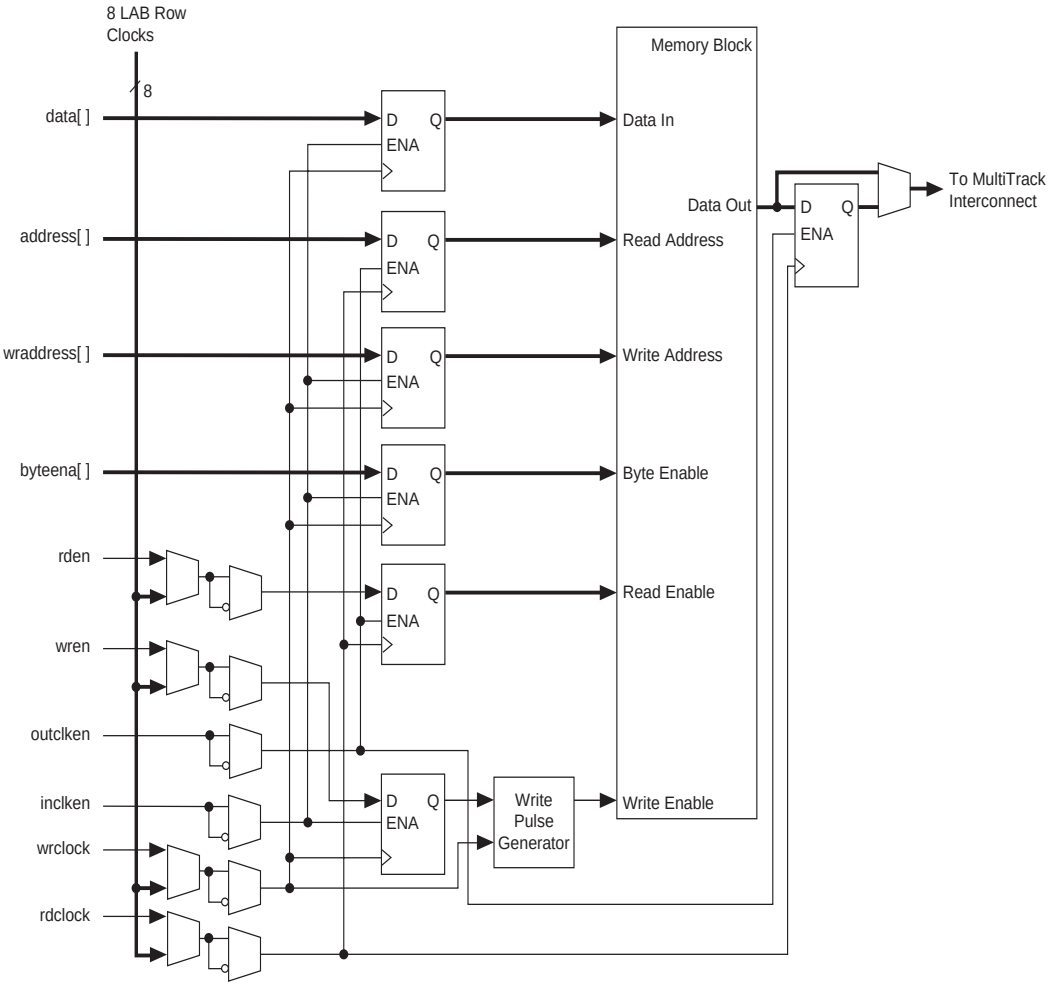


Figure 2–19. M-RAM Block Control Signals



One of the M-RAM block's horizontal sides drive the address and control signal (clock, renwe, byteena, etc.) inputs. Typically, the horizontal side closest to the device perimeter contains the interfaces. The one exception is when two M-RAM blocks are paired next to each other. In this case, the side of the M-RAM block opposite the common side of the two blocks contains the input interface. The top and bottom sides of any M-RAM block contain data input and output interfaces to the logic array. The top side has 72 data inputs and 72 data outputs for port B, and the bottom side has another 72 data inputs and 72 data outputs for port A. Figure 2–20 shows an example floorplan for the EP1S60 device and the location of the M-RAM interfaces.

Figure 2–27. Read/Write Clock Mode in Simple Dual-Port Mode Notes (1), (2)



Notes to Figure 2–27:

(1) All registers shown except the `rden` register have asynchronous clear ports.

(2) Violating the setup or hold time on the address registers could corrupt the memory contents. This applies to both read and write operations.

Table 2–13 shows the number of DSP blocks in each Stratix device.

Table 2–13. DSP Blocks in Stratix Devices Notes (1), (2)

Device	DSP Blocks	Total 9 × 9 Multipliers	Total 18 × 18 Multipliers	Total 36 × 36 Multipliers
EP1S10	6	48	24	6
EP1S20	10	80	40	10
EP1S25	10	80	40	10
EP1S30	12	96	48	12
EP1S40	14	112	56	14
EP1S60	18	144	72	18
EP1S80	22	176	88	22

Notes to Table 2–13:

(1) Each device has either the number of 9 × 9-, 18 × 18-, or 36 × 36-bit multipliers shown. The total number of multipliers for each device is not the sum of all the multipliers.

(2) The number of supported multiply functions shown is based on signed/signed or unsigned/unsigned implementations.

DSP block multipliers can optionally feed an adder/subtractor or accumulator within the block depending on the configuration. This makes routing to LEs easier, saves LE routing resources, and increases performance, because all connections and blocks are within the DSP block. Additionally, the DSP block input registers can efficiently implement shift registers for FIR filter applications.

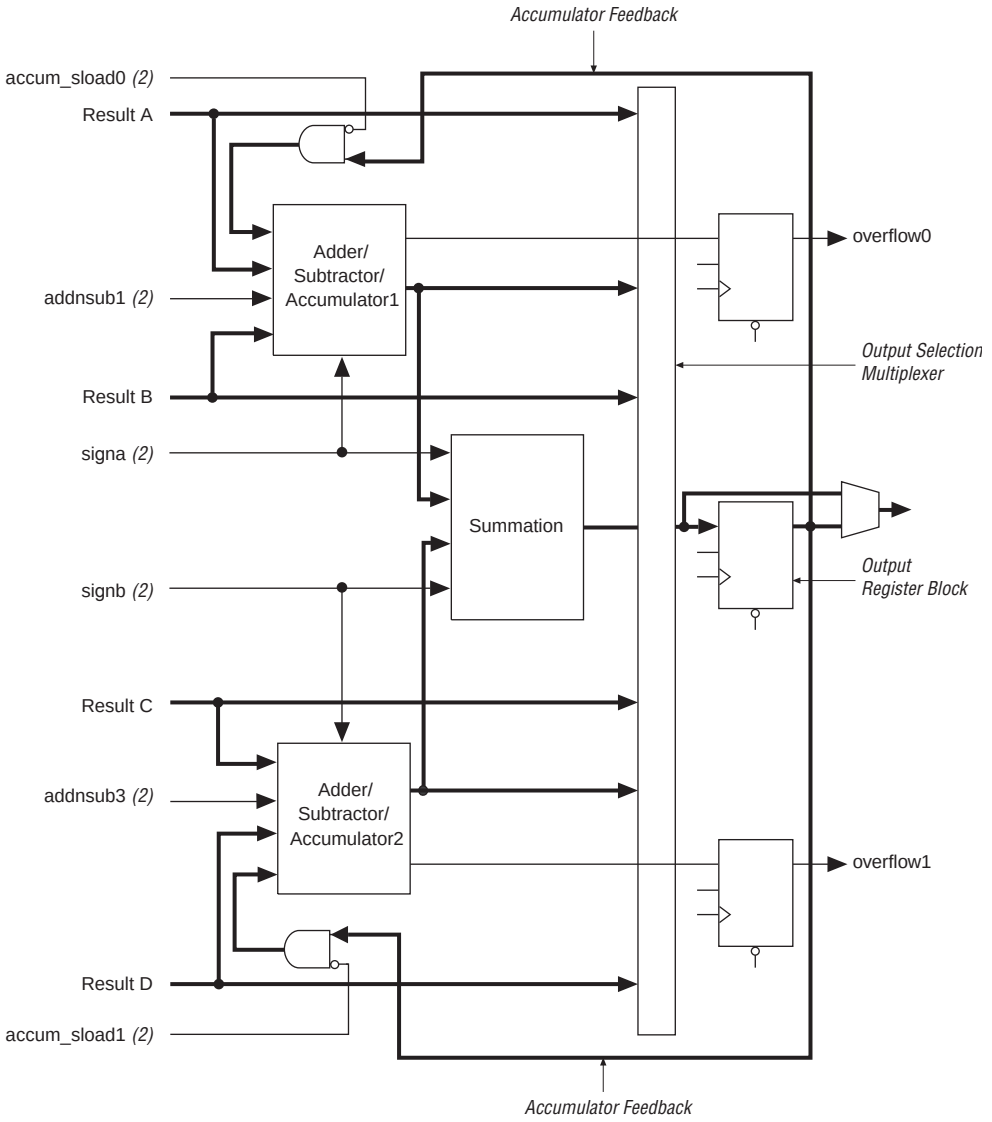
Figure 2–30 shows the top-level diagram of the DSP block configured for 18 × 18-bit multiplier mode. Figure 2–31 shows the 9 × 9-bit multiplier configuration of the DSP block.

Input Registers

A bank of optional input registers is located at the input of each multiplier and multiplicand inputs to the multiplier. When these registers are configured for parallel data inputs, they are driven by regular routing resources. You can use a clock signal, asynchronous clear signal, and a clock enable signal to independently control each set of A and B inputs for each multiplier in the DSP block. You select these control signals from a set of four different `clock[3..0]`, `aclr[3..0]`, and `ena[3..0]` signals that drive the entire DSP block.

You can also configure the input registers for a shift register application. In this case, the input registers feed the multiplier and drive two dedicated shift output lines: `shiftoutA` and `shiftoutB`. The shift outputs of one multiplier block directly feed the adjacent multiplier block in the same DSP block (or the next DSP block) as shown in Figure 2–33, to form a shift register chain. This chain can terminate in any block, that is, you can create any length of shift register chain up to 224 registers. You can use the input shift registers for FIR filter applications. One set of shift inputs can provide data for a filter, and the other are coefficients that are optionally loaded in serial or parallel. When implementing 9 × 9- and 18 × 18-bit multipliers, you do not need to implement external shift registers in LAB LEs. You implement all the filter circuitry within the DSP block and its routing resources, saving LE and general routing resources for general logic. External registers are needed for shift register inputs when using 36 × 36-bit multipliers.

Figure 2–34. Adder/Output Blocks *Note (1)*



Notes to Figure 2–34:

(1) Adder/output block shown in Figure 2–34 is in 18 × 18-bit mode. In 9 × 9-bit mode, there are four adder/subtractor blocks and two summation blocks.

(2) These signals are either not registered, registered once, or registered twice to match the data path pipeline.

The DSP block is divided into eight block units that interface with eight LAB rows on the left and right. Each block unit can be considered half of an 18 × 18-bit multiplier sub-block with 18 inputs and 18 outputs. A local interconnect region is associated with each DSP block. Like an LAB, this interconnect region can be fed with 10 direct link interconnects from the LAB to the left or right of the DSP block in the same row. All row and column routing resources can access the DSP block's local interconnect region. The outputs also work similarly to LAB outputs as well. Nine outputs from the DSP block can drive to the left LAB through direct link interconnects and nine can drive to the right LAB though direct link interconnects. All 18 outputs can drive to all types of row and column routing. Outputs can drive right- or left-column routing. Figures 2–40 and 2–41 show the DSP block interfaces to LAB rows.

Figure 2–40. DSP Block Interconnect Interface

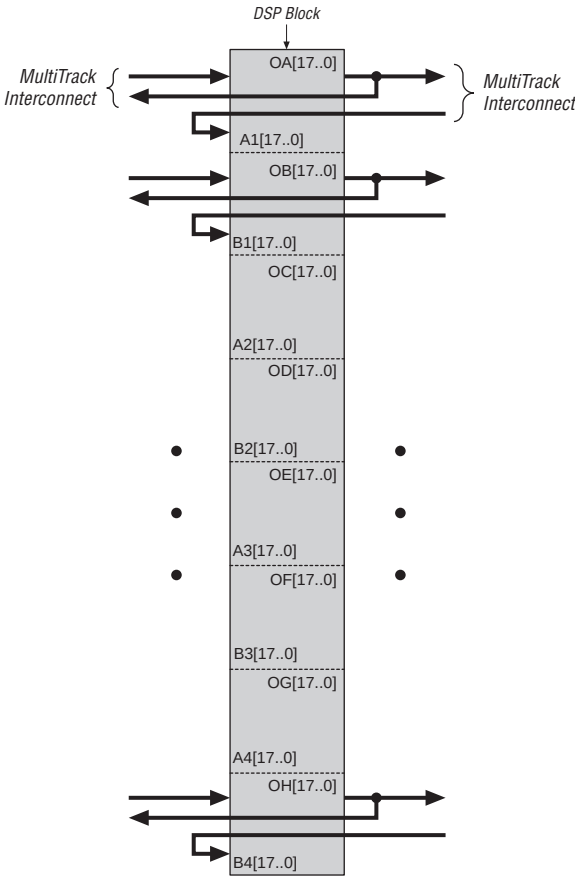
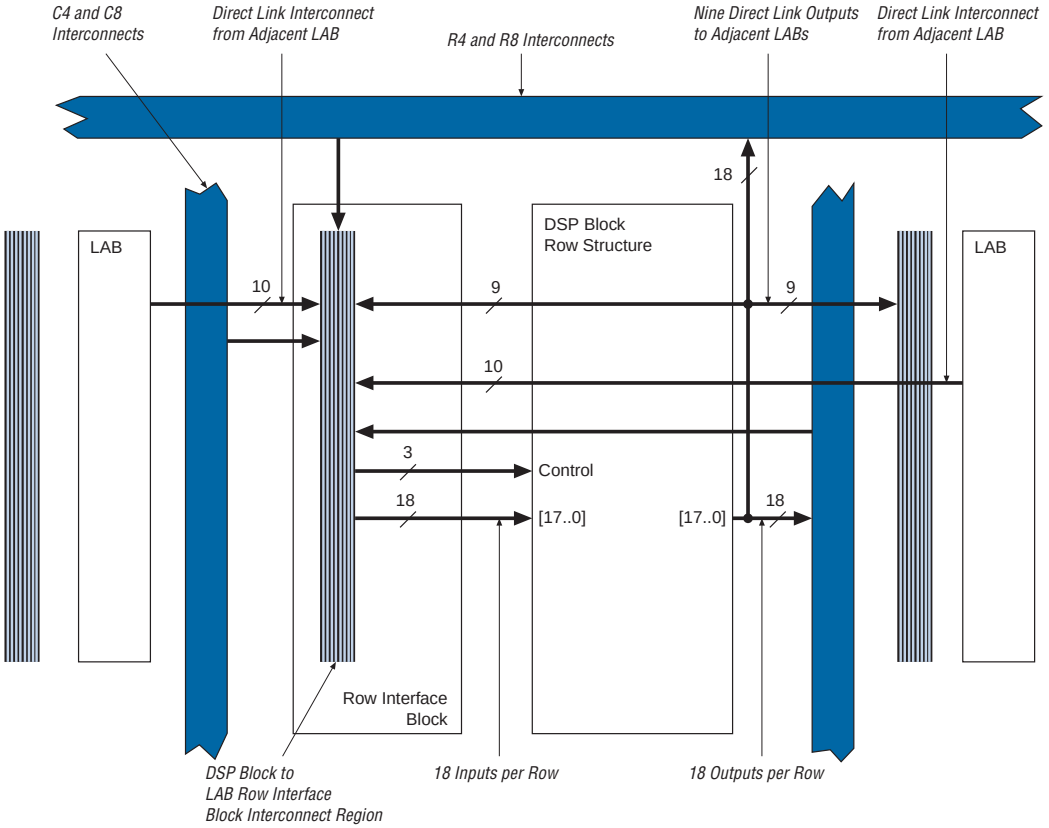
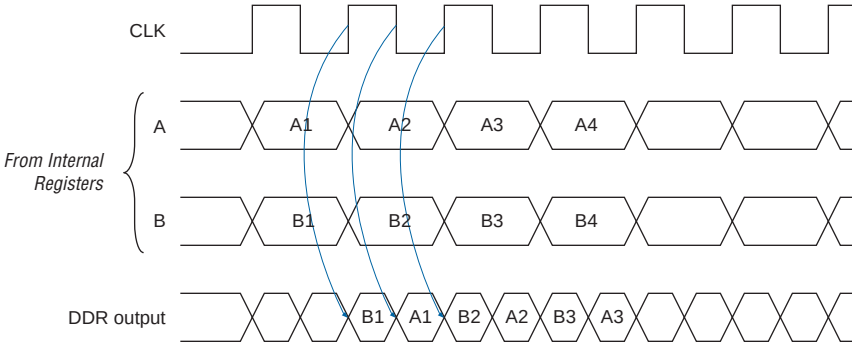


Figure 2–41. DSP Block Interface to Interconnect



A bus of 18 control signals feeds the entire DSP block. These signals include `clock[0..3]` clocks, `aclr[0..3]` asynchronous clears, `ena[1..4]` clock enables, `signa`, `signb` signed/unsigned control signals, `addnsub1` and `addnsub3` addition and subtraction control signals, and `accum_sload[0..1]` accumulator synchronous loads. The

Figure 2–68. Output Timing Diagram in DDR Mode



The Stratix IOE operates in bidirectional DDR mode by combining the DDR input and DDR output configurations. Stratix device I/O pins transfer data on a DDR bidirectional bus to support DDR SDRAM. The negative-edge-clocked OE register holds the OE signal inactive until the falling edge of the clock. This is done to meet DDR SDRAM timing requirements.

External RAM Interfacing

Stratix devices support DDR SDRAM at up to 200 MHz (400-Mbps data rate) through dedicated phase-shift circuitry, QDR and QDRII SRAM interfaces up to 167 MHz, and ZBT SRAM interfaces up to 200 MHz. Stratix devices also provide preliminary support for reduced latency DRAM II (RLDRAM II) at rates up to 200 MHz through the dedicated phase-shift circuitry.

In addition to the required signals for external memory interfacing, Stratix devices offer the optional clock enable signal. By default the Quartus II software sets the clock enable signal high, which tells the output register to update with new values. The output registers hold their own values if the design sets the clock enable signal low. See Figure 2–64.

To find out more about the DDR SDRAM specification, see the JEDEC web site (**www.jedec.org**). For information on memory controller megafunctions for Stratix devices, see the Altera web site (**www.altera.com**). See *AN 342: Interfacing DDR SDRAM with Stratix & Stratix GX Devices* for more information on DDR SDRAM interface in Stratix. Also see *AN 349: QDR SRAM Controller Reference Design for Stratix & Stratix GX Devices* and *AN 329: ZBT SRAM Controller Reference Design for Stratix & Stratix GX Devices*.

Table 2–26. External RAM Support in EP1S60 & EP1S80 Devices

DDR Memory Type	I/O Standard	Maximum Clock Rate (MHz)		
		-5 Speed Grade	-6 Speed Grade	-7 Speed Grade
DDR SDRAM *(1)*, *(2)*	SSTL-2	167	167	133
DDR SDRAM - side banks *(2)*, *(3)*	SSTL-2	150	133	133
QDR SRAM *(4)*	1.5-V HSTL	133	133	133
QDRII SRAM *(4)*	1.5-V HSTL	167	167	133
ZBT SRAM *(5)*	LVTTL	200	200	167

Notes to Table 2–26:

(1) These maximum clock rates apply if the Stratix device uses DQS phase-shift circuitry to interface with DDR SDRAM. DQS phase-shift circuitry is only available in the top and bottom I/O banks (I/O banks 3, 4, 7, and 8).

(2) For more information on DDR SDRAM, see *AN 342: Interfacing DDR SDRAM with Stratix & Stratix GX Devices*.

(3) DDR SDRAM is supported on the Stratix device side I/O banks (I/O banks 1, 2, 5, and 6) without dedicated DQS phase-shift circuitry. The read DQS signal is ignored in this mode. Numbers are preliminary.

(4) For more information on QDR or QDRII SRAM, see *AN 349: QDR SRAM Controller Reference Design for Stratix & Stratix GX Devices*.

(5) For more information on ZBT SRAM, see *AN 329: ZBT SRAM Controller Reference Design for Stratix & Stratix GX Devices*.

In addition to six I/O registers and one input latch in the IOE for interfacing to these high-speed memory interfaces, Stratix devices also have dedicated circuitry for interfacing with DDR SDRAM. In every Stratix device, the I/O banks at the top (I/O banks 3 and 4) and bottom (I/O banks 7 and 8) of the device support DDR SDRAM up to 200 MHz. These pins support DQS signals with DQ bus modes of ×8, ×16, or ×32.

Table 2–27 shows the number of DQ and DQS buses that are supported per device.

Table 2–27. DQS & DQ Bus Mode Support (Part 1 of 2) Note (1)

Device	Package	Number of ×8 Groups	Number of ×16 Groups	Number of ×32 Groups
EP1S10	672-pin BGA 672-pin FineLine BGA	12 *(2)*	0	0
	484-pin FineLine BGA 780-pin FineLine BGA	16 *(3)*	0	4
EP1S20	484-pin FineLine BGA	18*(4)*	7 *(5)*	4
	672-pin BGA 672-pin FineLine BGA	16*(3)*	7 *(5)*	4
	780-pin FineLine BGA	20	7 *(5)*	4

- 1.8-V HSTL Class I and II
- SSTL-3 Class I and II
- SSTL-2 Class I and II
- SSTL-18 Class I and II
- CTT

Table 2–31 describes the I/O standards supported by Stratix devices.

Table 2–31. Stratix Supported I/O Standards

I/O Standard	Type	Input Reference Voltage (V_{REF}) (V)	Output Supply Voltage (V_{CCIO}) (V)	Board Termination Voltage (V_{TT}) (V)
LVTTL	Single-ended	N/A	3.3	N/A
LVCMOS	Single-ended	N/A	3.3	N/A
2.5 V	Single-ended	N/A	2.5	N/A
1.8 V	Single-ended	N/A	1.8	N/A
1.5 V	Single-ended	N/A	1.5	N/A
3.3-V PCI	Single-ended	N/A	3.3	N/A
3.3-V PCI-X 1.0	Single-ended	N/A	3.3	N/A
LVDS	Differential	N/A	3.3	N/A
LVPECL	Differential	N/A	3.3	N/A
3.3-V PCML	Differential	N/A	3.3	N/A
HyperTransport	Differential	N/A	2.5	N/A
Differential HSTL *(1)*	Differential	0.75	1.5	0.75
Differential SSTL *(2)*	Differential	1.25	2.5	1.25
GTL	Voltage-referenced	0.8	N/A	1.20
GTL+	Voltage-referenced	1.0	N/A	1.5
1.5-V HSTL Class I and II	Voltage-referenced	0.75	1.5	0.75
1.8-V HSTL Class I and II	Voltage-referenced	0.9	1.8	0.9
SSTL-18 Class I and II	Voltage-referenced	0.90	1.8	0.90
SSTL-2 Class I and II	Voltage-referenced	1.25	2.5	1.25
SSTL-3 Class I and II	Voltage-referenced	1.5	3.3	1.5
AGP (1× and 2°)	Voltage-referenced	1.32	3.3	N/A
CTT	Voltage-referenced	1.5	3.3	1.5

Notes to Table 2–31:
(1) This I/O standard is only available on input and output clock pins.
(2) This I/O standard is only available on output column clock pins.

However, there is additional resistance present between the device ball and the input of the receiver buffer, as shown in Figure 2–72. This resistance is because of package trace resistance (which can be calculated as the resistance from the package ball to the pad) and the parasitic layout metal routing resistance (which is shown between the pad and the intersection of the on-chip termination and input buffer).

Figure 2–72. Differential Resistance of LVDS Differential Pin Pair (R_D)

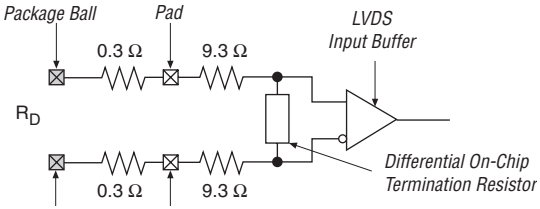


Table 2–35 defines the specification for internal termination resistance for commercial devices.

Table 2–35. Differential On-Chip Termination

Symbol	Description	Conditions	Resistance			Unit
			Min	Typ	Max	
R_D *(2)*	Internal differential termination for LVDS	Commercial *(1)*, *(3)*	110	135	165	W
		Industrial *(2)*, *(3)*	100	135	170	W

Notes to Table 2–35:

(1) Data measured over minimum conditions (T_j = 0 C, V_{CCIO} +5%) and maximum conditions (T_j = 85 C, V_{CCIO} = –5%).

(2) Data measured over minimum conditions (T_j = –40 C, V_{CCIO} +5%) and maximum conditions (T_j = 100 C, V_{CCIO} = –5%).

(3) LVDS data rate is supported for 840 Mbps using internal differential termination.

MultiVolt I/O Interface

The Stratix architecture supports the MultiVolt I/O interface feature, which allows Stratix devices in all packages to interface with systems of different supply voltages.

The Stratix VCCINT pins must always be connected to a 1.5-V power supply. With a 1.5-V V_{CCINT} level, input pins are 1.5-V, 1.8-V, 2.5-V, and 3.3-V tolerant. The VCCIO pins can be connected to either a 1.5-V, 1.8-V, 2.5-V, or 3.3-V power supply, depending on the output requirements.

Table 2–37. EP1S10, EP1S20 & EP1S25 Device Differential Channels (Part 2 of 2) Note (1)

Device	Package	Transmitter/ Receiver	Total Channels	Maximum Speed (Mbps)	Center Fast PLLs			
					PLL 1	PLL 2	PLL 3	PLL 4
EP1S25	672-pin FineLine BGA 672-pin BGA	Transmitter (2)	56	624 (4)	14	14	14	14
				624 (3)	28	28	28	28
		Receiver	58	624 (4)	14	15	15	14
				624 (3)	29	29	29	29
	780-pin FineLine BGA	Transmitter (2)	70	840 (4)	18	17	17	18
				840 (3)	35	35	35	35
		Receiver	66	840 (4)	17	16	16	17
				840 (3)	33	33	33	33
	1,020-pin FineLine BGA	Transmitter (2)	78	840 (4)	19	20	20	19
				840 (3)	39	39	39	39
		Receiver	78	840 (4)	19	20	20	19
				840 (3)	39	39	39	39

Notes to Table 2–37:

(1) The first row for each transmitter or receiver reports the number of channels driven directly by the PLL. The second row below it shows the maximum channels a PLL can drive if cross bank channels are used from the adjacent center PLL. For example, in the 484-pin FineLine BGA EP1S10 device, PLL 1 can drive a maximum of five channels at 840 Mbps or a maximum of 10 channels at 840 Mbps. The Quartus II software may also merge receiver and transmitter PLLs when a receiver is driving a transmitter. In this case, one fast PLL can drive both the maximum numbers of receiver and transmitter channels.

(2) The number of channels listed includes the transmitter clock output (`tx_outclock`) channel. If the design requires a DDR clock, it can use an extra data channel.

(3) These channels span across two I/O banks per side of the device. When a center PLL clocks channels in the opposite bank on the same side of the device it is called cross-bank PLL support. Both center PLLs can clock cross-bank channels simultaneously if, for example, PLL_1 is clocking all receiver channels and PLL_2 is clocking all transmitter channels. You cannot have two adjacent PLLs simultaneously clocking cross-bank receiver channels or two adjacent PLLs simultaneously clocking transmitter channels. Cross-bank allows for all receiver channels on one side of the device to be clocked on one clock while all transmitter channels on the device are clocked on the other center PLL. Crossbank PLLs are supported at full-speed, 840 Mbps. For wire-bond devices, the full-speed is 624 Mbps.

(4) These values show the channels available for each PLL without crossing another bank.

When you span two I/O banks using cross-bank support, you can route only two load enable signals total between the PLLs. When you enable `rx_data_align`, you use both `rxloadena` and `txloadena` of a PLL. That leaves no `loadena` for the second PLL.

Table 4–10. 3.3-V LVDS I/O Specifications (Part 2 of 2)

Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Unit
V_{ICM}	Input common mode voltage *(6)*	LVDS 0.3 V ≤V_{ID} ≤1.0 V *W* = 1 through 10	100		1,100	mV
		LVDS 0.3 V ≤V_{ID} ≤1.0 V *W* = 1 through 10	1,600		1,800	mV
		LVDS 0.2 V ≤V_{ID} ≤1.0 V *W* = 1	1,100		1,600	mV
		LVDS 0.1 V ≤V_{ID} ≤1.0 V *W* = 2 through 10	1,100		1,600	mV
V_{OD} *(1)*	Output differential voltage (single-ended)	R_L = 100 Ω	250	375	550	mV
Δ V_{OD}	Change in V_{OD} between high and low	R_L = 100 Ω			50	mV
V_{OCM}	Output common mode voltage	R_L = 100 Ω	1,125	1,200	1,375	mV
Δ V_{OCM}	Change in V_{OCM} between high and low	R_L = 100 Ω			50	mV
R_L	Receiver differential input discrete resistor (external to Stratix devices)		90	100	110	Ω

Table 4–43. Routing Delay Internal Timing Microparameter Descriptions (Part 2 of 2)

Symbol	Parameter
t_{C4}	Delay for a C4 line with average loading; covers a distance of four LAB rows.
t_{C8}	Delay for a C8 line with average loading; covers a distance of eight LAB rows.
t_{C16}	Delay for a C16 line with average loading; covers a distance of 16 LAB rows.
t_{LOCAL}	Local interconnect delay, for connections within a LAB, and for the final routing hop of connections to LABs, DSP blocks, RAM blocks and I/Os.

Table 4–44. LE Internal Timing Microparameters

Parameter	-5		-6		-7		-8		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{SU}	10		10		11		13		ps
t_{H}	100		100		114		135		ps
t_{CO}		156		176		202		238	ps
t_{LUT}		366		459		527		621	ps
t_{CLR}	100		100		114		135		ps
t_{PRE}	100		100		114		135		ps
t_{CLKHL}	1000		1111		1190		1400		ps

Table 4–45. IOE Internal TSU Microparameter by Device Density (Part 1 of 2)

Device	Symbol	-5		-6		-7		-8		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
EP1S10	t_{SU_R}	76		80		80		80		ps
	t_{SU_C}	176		80		80		80		ps
EP1S20	t_{SU_R}	76		80		80		80		ps
	t_{SU_C}	76		80		80		80		ps
EP1S25	t_{SU_R}	276		280		280		280		ps
	t_{SU_C}	276		280		280		280		ps
EP1S30	t_{SU_R}	76		80		80		80		ps
	t_{SU_C}	176		180		180		180		ps

Table 4–52 shows the external I/O timing parameters when using fast regional clock networks.

Table 4–52. Stratix Fast Regional Clock External I/O Timing Parameters Notes (1), (2)

Symbol	Parameter
t_{INSU}	Setup time for input or bidirectional pin using IOE input register with fast regional clock fed by FCLK pin
t_{INH}	Hold time for input or bidirectional pin using IOE input register with fast regional clock fed by FCLK pin
t_{OUTCO}	Clock-to-output delay output or bidirectional pin using IOE output register with fast regional clock fed by FCLK pin
t_{XZ}	Synchronous IOE output enable register to output pin disable delay using fast regional clock fed by FCLK pin
t_{ZX}	Synchronous IOE output enable register to output pin enable delay using fast regional clock fed by FCLK pin

Notes to Table 4–52:
(1) These timing parameters are sample-tested only.
(2) These timing parameters are for column and row IOE pins. You should use the Quartus II software to verify the external timing for any pin.

Table 4–53 shows the external I/O timing parameters when using regional clock networks.

Table 4–53. Stratix Regional Clock External I/O Timing Parameters (Part 1 of 2) Notes (1), (2)

Symbol	Parameter
t_{INSU}	Setup time for input or bidirectional pin using IOE input register with regional clock fed by CLK pin
t_{INH}	Hold time for input or bidirectional pin using IOE input register with regional clock fed by CLK pin
t_{OUTCO}	Clock-to-output delay output or bidirectional pin using IOE output register with regional clock fed by CLK pin
$t_{INSUPLL}$	Setup time for input or bidirectional pin using IOE input register with regional clock fed by Enhanced PLL with default phase setting
t_{INHPLL}	Hold time for input or bidirectional pin using IOE input register with regional clock fed by Enhanced PLL with default phase setting
$t_{OUTCOPLL}$	Clock-to-output delay output or bidirectional pin using IOE output register with regional clock Enhanced PLL with default phase setting

Stratix External I/O Timing

These timing parameters are for both column IOE and row IOE pins. In EP1S30 devices and above, you can decrease the t_{SU} time by using the FPLLCLK, but may get positive hold time in EP1S60 and EP1S80 devices. You should use the Quartus II software to verify the external devices for any pin.

Tables 4–55 through 4–60 show the external timing parameters on column and row pins for EP1S10 devices.

Table 4–55. EP1S10 External I/O Timing on Column Pins Using Fast Regional Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
t_{INSU}	2.238		2.325		2.668		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.240	4.549	2.240	4.836	2.240	5.218	NA	NA	ns
t_{XZ}	2.180	4.423	2.180	4.704	2.180	5.094	NA	NA	ns
t_{ZX}	2.180	4.423	2.180	4.704	2.180	5.094	NA	NA	ns

Table 4–56. EP1S10 External I/O Timing on Column Pins Using Regional Clock Networks *Note (1)*

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max			
t_{INSU}	1.992		2.054		2.359		NA		ns
t_{INH}	0.000		0.000		0.000		NA		ns
t_{OUTCO}	2.395	4.795	2.395	5.107	2.395	5.527	NA	NA	ns
t_{XZ}	2.335	4.669	2.335	4.975	2.335	5.403	NA	NA	ns
t_{ZX}	2.335	4.669	2.335	4.975	2.335	5.403	NA	NA	ns
$t_{INSUPLL}$	0.975		0.985		1.097		NA		ns
t_{INHPLL}	0.000		0.000		0.000		NA	NA	ns
$t_{OUTCOPLL}$	1.262	2.636	1.262	2.680	1.262	2.769	NA	NA	ns
t_{XZPLL}	1.202	2.510	1.202	2.548	1.202	2.645	NA	NA	ns
t_{ZXPLL}	1.202	2.510	1.202	2.548	1.202	2.645	NA	NA	ns

Table 4–105. Stratix I/O Standard Output Delay Adders for Fast Slew Rate on Column Pins (Part 2 of 2)

Parameter	-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
	Min	Max	Min	Max	Min	Max	Min	Max	
CTT		973		1,021		1,021		1,021	ps
SSTL-3 Class I		719		755		755		755	ps
SSTL-3 Class II		146		153		153		153	ps
SSTL-2 Class I		678		712		712		712	ps
SSTL-2 Class II		223		234		234		234	ps
SSTL-18 Class I		1,032		1,083		1,083		1,083	ps
SSTL-18 Class II		447		469		469		469	ps
1.5-V HSTL Class I		660		693		693		693	ps
1.5-V HSTL Class II		537		564		564		564	ps
1.8-V HSTL Class I		304		319		319		319	ps
1.8-V HSTL Class II		231		242		242		242	ps

Table 4–106. Stratix I/O Standard Output Delay Adders for Fast Slew Rate on Row Pins (Part 1 of 2)

Parameter		-5 Speed Grade		-6 Speed Grade		-7 Speed Grade		-8 Speed Grade		Unit
		Min	Max	Min	Max	Min	Max	Min	Max	
LVCMOS	2 mA		1,518		1,594		1,594		1,594	ps
	4 mA		746		783		783		783	ps
	8 mA		96		100		100		100	ps
	12 mA		0		0		0		0	ps
3.3-V LVTTL	4 mA		1,518		1,594		1,594		1,594	ps
	8 mA		1,038		1,090		1,090		1,090	ps
	12 mA		521		547		547		547	ps
	16 mA		414		434		434		434	ps
	24 mA		0		0		0		0	ps
2.5-V LVTTL	2 mA		2,032		2,133		2,133		2,133	ps
	8 mA		699		734		734		734	ps
	12 mA		374		392		392		392	ps
	16 mA		165		173		173		173	ps
1.8-V LVTTL	2 mA		3,714		3,899		3,899		3,899	ps
	8 mA		1,055		1,107		1,107		1,107	ps
	12 mA		830		871		871		871	ps

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